

**SEBT8050**

**EPITAXIAL PLANAR PNP TRANSISTOR**

**Features**

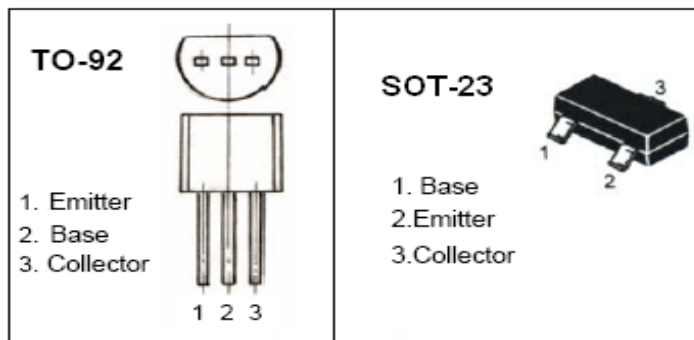
- Complementary to SEBT8050

**Applications**

- HIGH CURRENT APPLICATION

**Construction**

- 



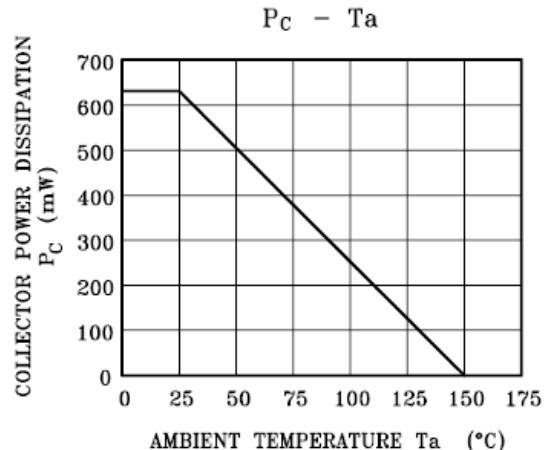
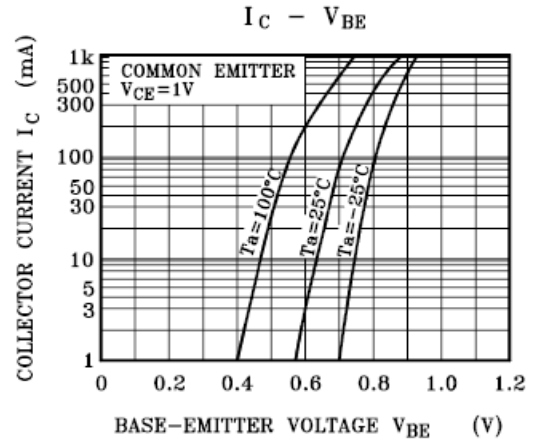
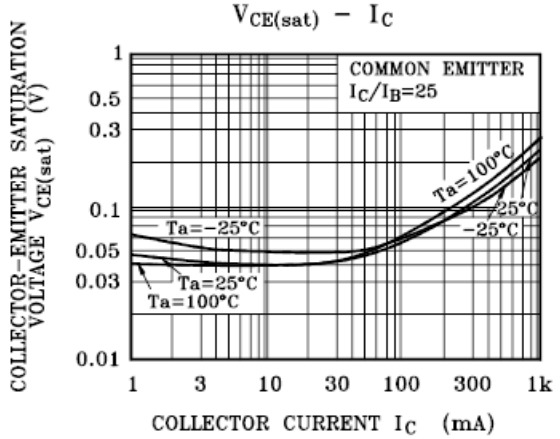
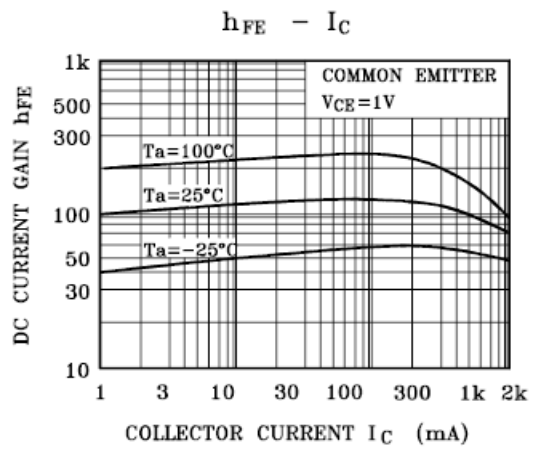
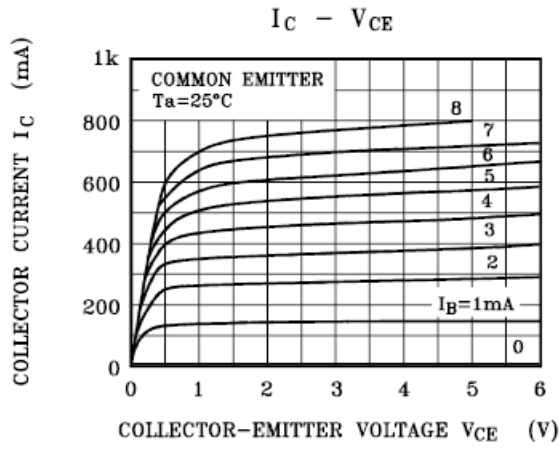
**Maximum Ratings (Ta=25°C)**

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	$V_{CBO}$	35	V
Collector-Emitter Voltage	$V_{CEO}$	30	V
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1500	mA
Emitter Current	$I_E$	-800	mA
Collector Power Dissipation	$P_C$	625	mW
Junction temperature	$T_j$	150	°C
Storage temperature Range	$T_{stg}$	-55 ~ +150	°C

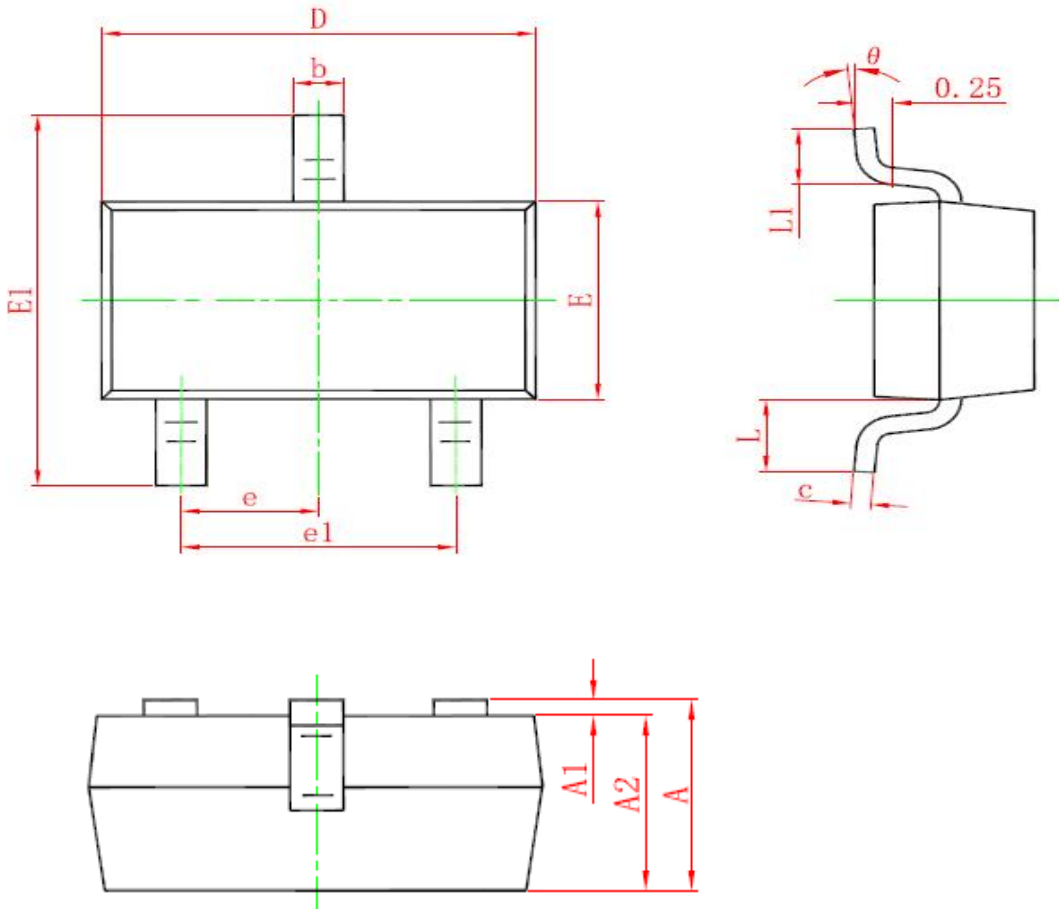
**Electrical characteristics (Ta=25°C)**

Characteristic	Symbol	Test Condition	MIN	TYP.	MAX	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=15v$	-	-	50	nA
Collector-Base Breakdown Voltage	$V_{(BR) CBO}$	$I_C=0.5mA$	-35	-	-	V
Collector-Emitter Breakdown Voltage	$V_{(BR) CEO}$	$I_C=1mA$	-30	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=1v, I_C=50mA$	100	-	300	
	$h_{FE(2)}$	$V_{CE}=1v, I_C=350mA$	60	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=20mA$	-	-	0.5	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=1v, I_C=500mA$	-	-	1.2	V
Transition Frequency	$f_T$	$V_{CE}=5v, I_C=10mA$	-	120	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, f=1MHz,$	-	13	-	pF

Note:  $h_{FE(1)}$  Classification C : 100~200, D : 150~300

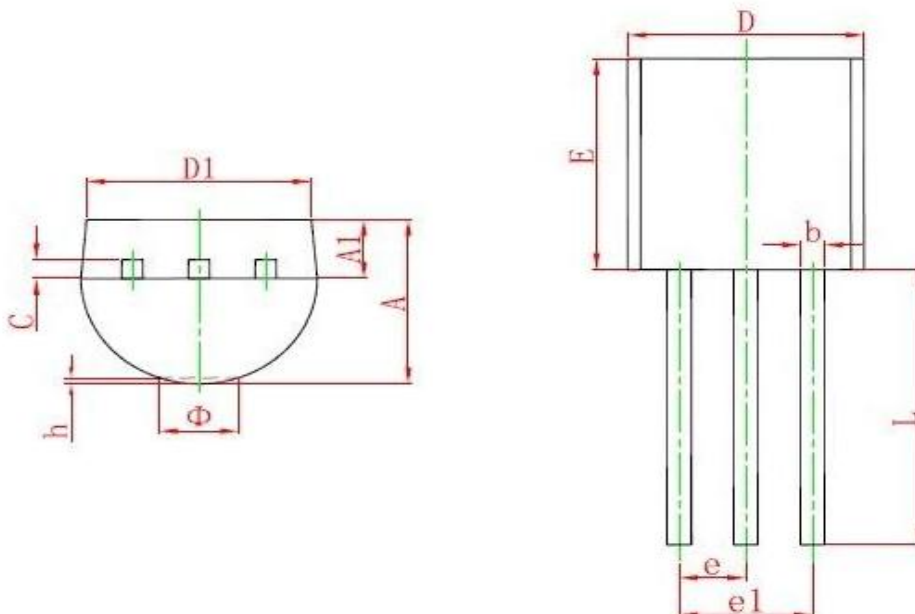


SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

**TO-92 PACKAGE OUTLINE DIMENSIONS**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270 TYP		0.050 TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
$\Phi$		1.600		0.063
h	0.000	0.380	0.000	0.015

The SINO-IC logo is a registered trademark of ShangHai Sino-IC Microelectronics Co., Ltd.

© 2005 SINO-IC – Printed in China – All rights reserved.

**SHANGHAI SINO-IC MICROELECTRONICS CO., LTD**

**Add:** Building 3, Room 3401-03, No.200 Zhangheng Road, ZhangJiang Hi-Tech Park, Pudong, Shanghai 201203, China

**Phone:** +86-21-33932402 33932403 33932405 33933508 33933608

**Fax:** +86-21-33932401

**Email:** szrxw002@126.com

**Website:** <http://www.sino-ic.net>